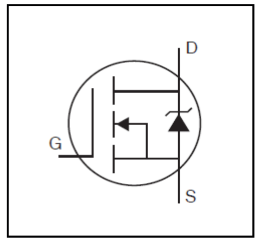
IRFI4110GPbF

HEXFET® Power MOSFET

Applications
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



V_{DSS}	**100V**
$R_{DS(on)}$ typ.	**3.7mΩ**
$R_{DS(on)}$ max.	**4.5mΩ**
I_D	**72A**

Benefits
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free
- Halogen-Free

TO-220 Full-Pak

G	D	S
Gate	Drain	Source

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFI4110GPbF	TO-220 Full-Pak	Tube	50	IRFI4110GPbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	72	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	51	
I_{DM}	Pulsed Drain Current ①	290	
P_D @T_C = 25°C	Maximum Power Dissipation	61	W
	Linear Derating Factor	0.41	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt③	27	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Avalanche Characteristics

E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	71	mJ
I_{AR}	Avalanche Current ①	43	A
E_{AR}	Repetitive Avalanche Energy ①	6.1	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	——	2.46	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount)⑦	——	65	

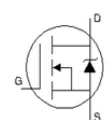
Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.11	——	V/°C	Reference to 25°C, I_D = 5mA ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	3.7	4.5	mΩ	V_{GS} = 10V, I_D = 43A
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source Leakage Current	——	——	20	μA	V_{DS} = 100 V, V_{GS} = 0V
		——	——	250		V_{DS} = 100V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V

Dynamic @ T_J = 25°C (unless otherwise specified)

gfs	Forward Trans conductance	260	——	——	S	V_{DS} = 50V, I_D = 43A
Q_g	Total Gate Charge	——	190	290	nC	I_D = 43A
Q_{gs}	Gate-to-Source Charge	——	40	——		V_{DS} = 50V
Q_{gd}	Gate-to-Drain Charge	——	49	——		V_{GS} = 10V ④
R_G	Internal Gate Resistance	——	1.3	——	Ω	
$t_{d(on)}$	Turn-On Delay Time	——	24	——	ns	V_{DD} = 65V
t_r	Rise Time	——	58	——		I_D = 43A
$t_{d(off)}$	Turn-Off Delay Time	——	81	——		R_G= 2.6Ω
t_f	Fall Time	——	71	——		V_{GS} = 10V ④
C_{iss}	Input Capacitance	——	9540	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	680	——		V_{DS} = 50V
C_{rss}	Reverse Transfer Capacitance	——	300	——		f = 1.0MHz
$C_{oss\ eff.\ (ER)}$	Effective Output Capacitance (Energy Related)	——	760	——		V_{GS}=0V,V_{DS}= 0V to 80V ⑥
$C_{oss\ eff.\ (TR)}$	Effective Output Capacitance (Time Related)	——	1120	——		V_{GS} = 0V, V_{DS} = 0V to 80V ⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	72	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	290		
V_{SD}	Diode Forward Voltage	——	——	1.3	V	T_J = 25°C,I_S = 43A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	50	75	ns	T_J = 25°C
		——	60	90		T_J = 125°C; V_R = 85V
Q_{rr}	Reverse Recovery Charge	——	100	150	nC	T_J = 25°C; I_F = 43A
		——	140	210		T_J = 125°C; di/dt= 100A/μs④
I_{RRM}	Reverse Recovery Current	——	3.5	——	A	T_J = 25°C
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.077mH, R_G = 50Ω, I_{AS} = 43A, V_{GS} =10V. Part not recommended for use above this value.
③ $I_{SD} \leq$ 43A, di/dt $\leq$ 1600A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.
④ Pulse width $\leq$ 400μs; duty cycle $\leq$ 2%.
⑤ $C_{oss\ eff.}$ (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑥ $C_{oss\ eff.}$ (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
⑧ R_θ is measured at T_J approximately 90°C.

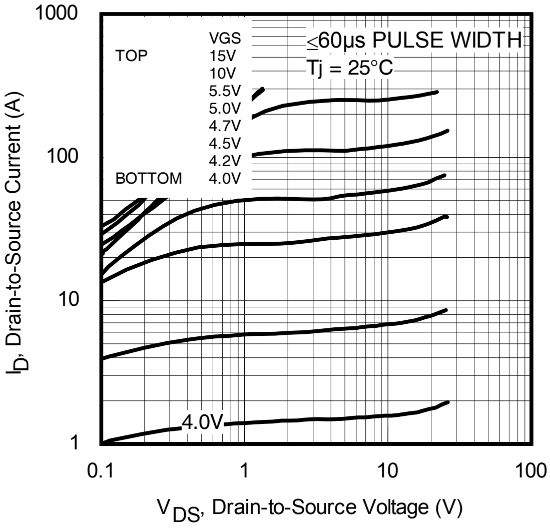


Fig. 1 Typical Output Characteristics

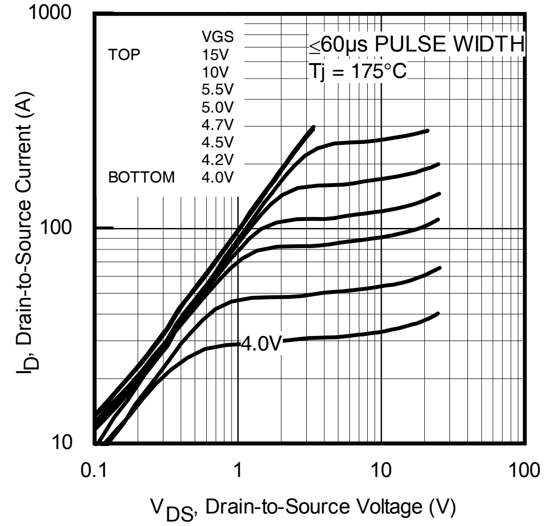


Fig. 2 Typical Output Characteristics

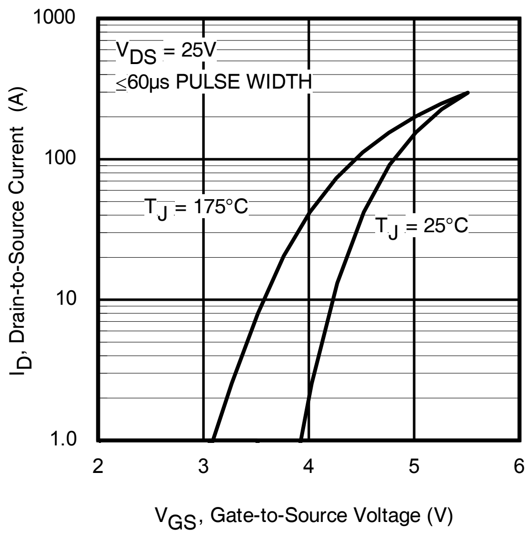


Fig. 3 Typical Transfer Characteristics

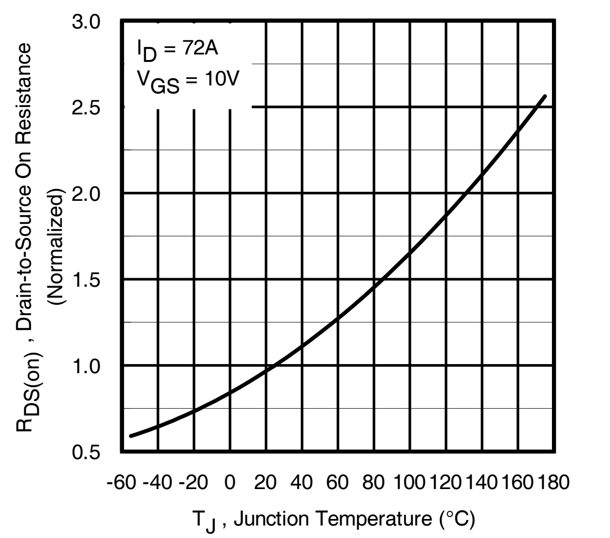


Fig. 4 Normalized On-Resistance vs. Temperature

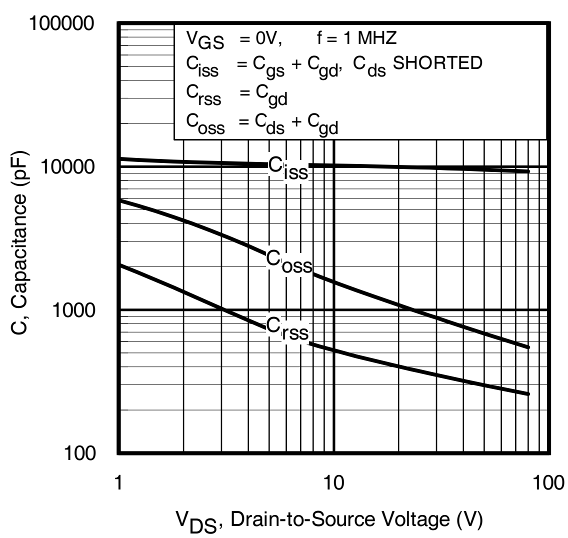


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

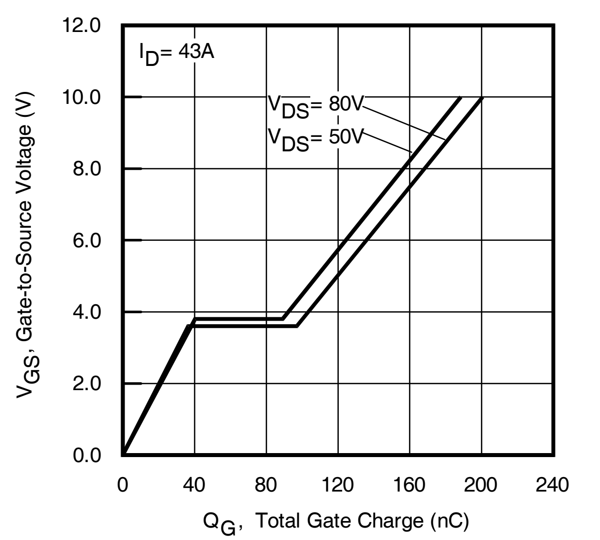


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

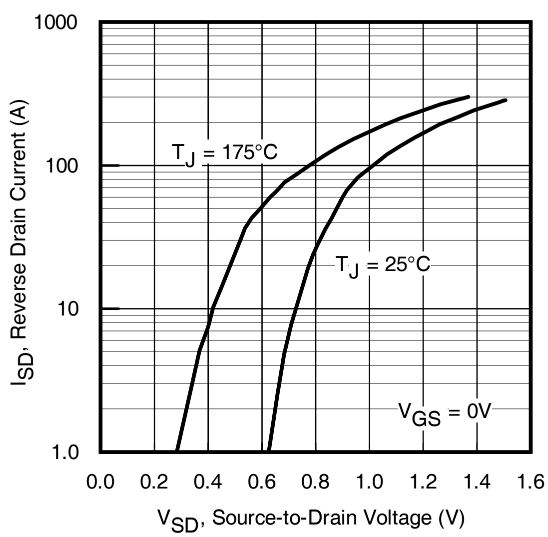


Fig. 7. Typical Source-to-Drain Diode Forward Voltage

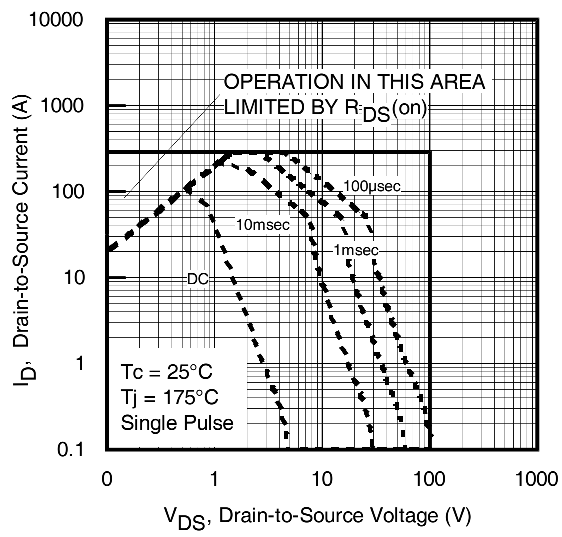


Fig 8. Maximum Safe Operating Area

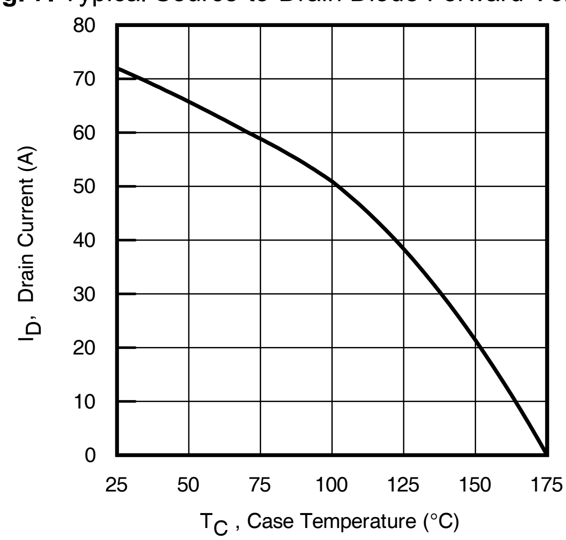


Fig. 9. Maximum Drain Current vs. Case Temperature

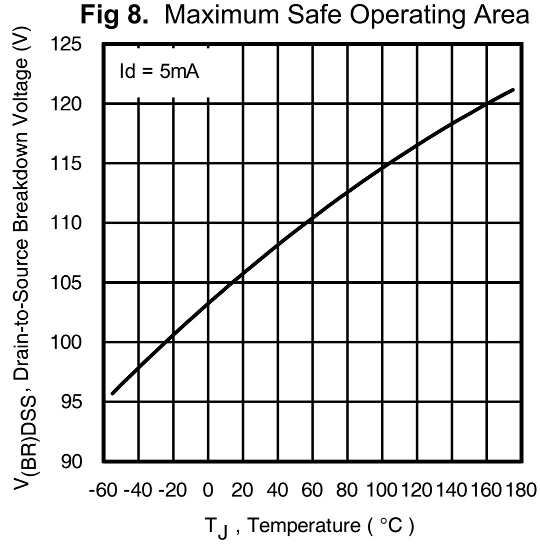


Fig 10. Drain-to-Source Breakdown Voltage

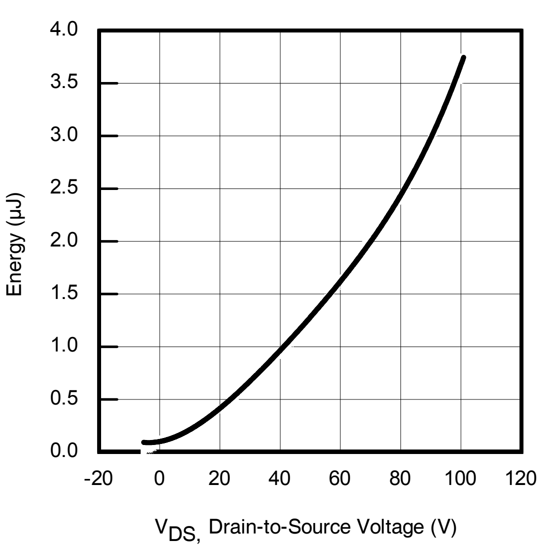


Fig. 11. Typical C_{OSS} Stored Energy

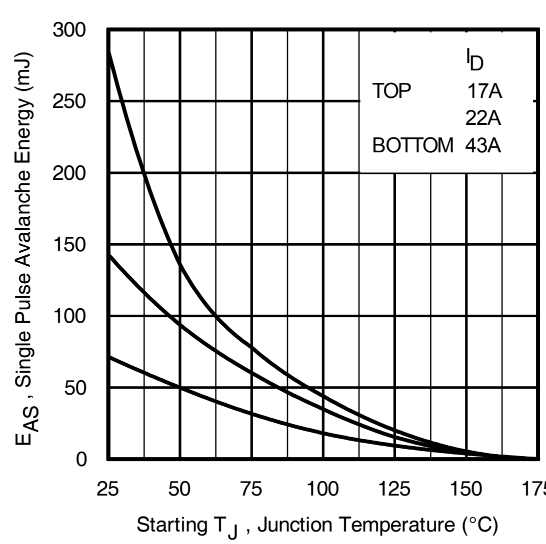


Fig 12. Maximum Avalanche Energy vs. Drain Current

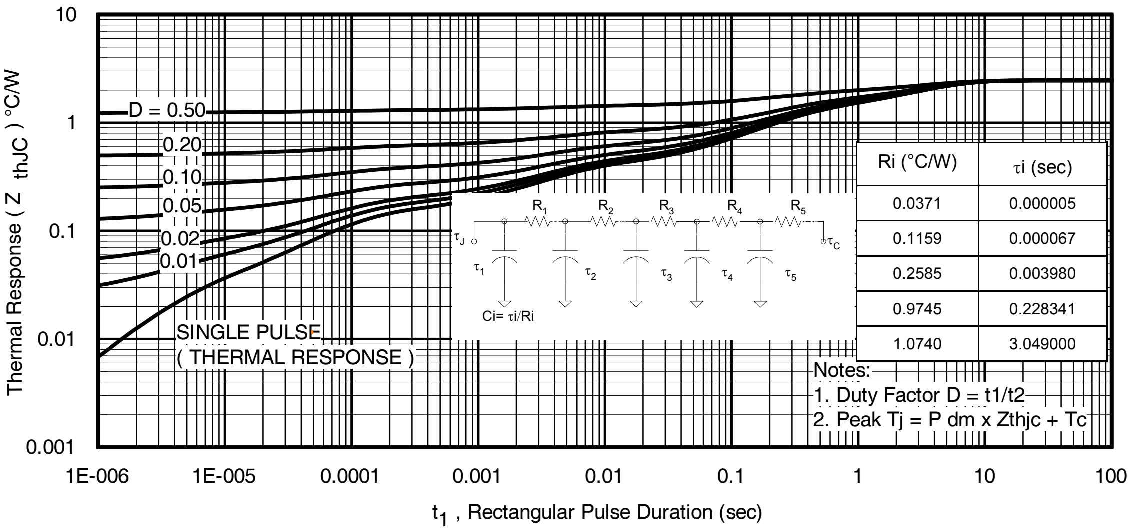


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

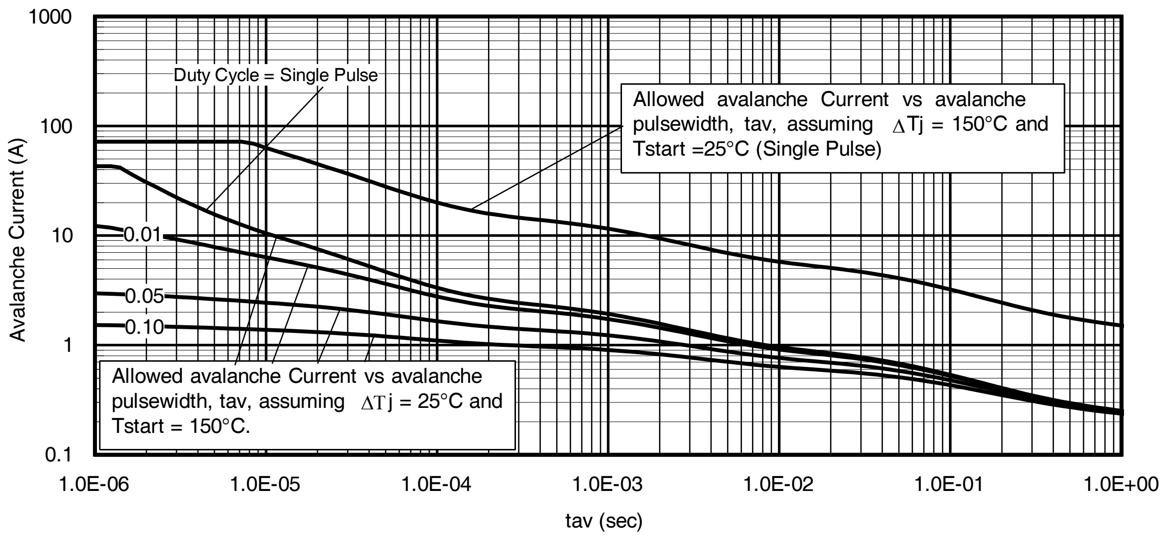


Fig 14. Single Avalanche Event: Pulse Current vs. Pulse Width

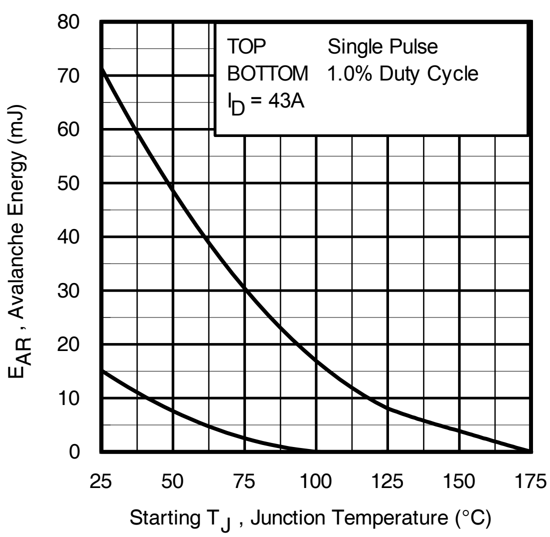


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = tav ·f
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

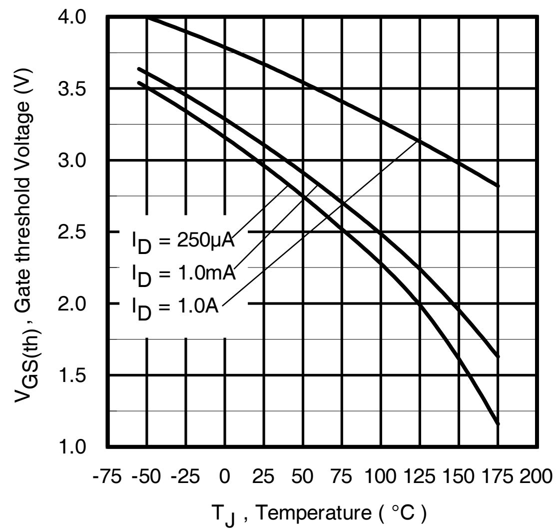


Fig 16. Threshold Voltage vs. Temperature

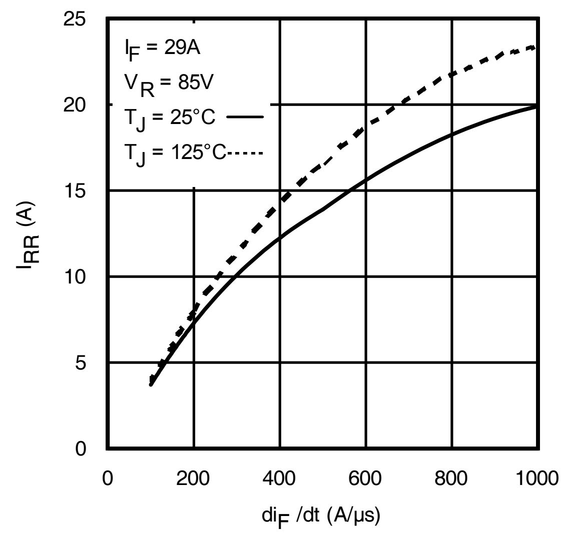


Fig 17. Typical Recovery Current vs. dif/dt

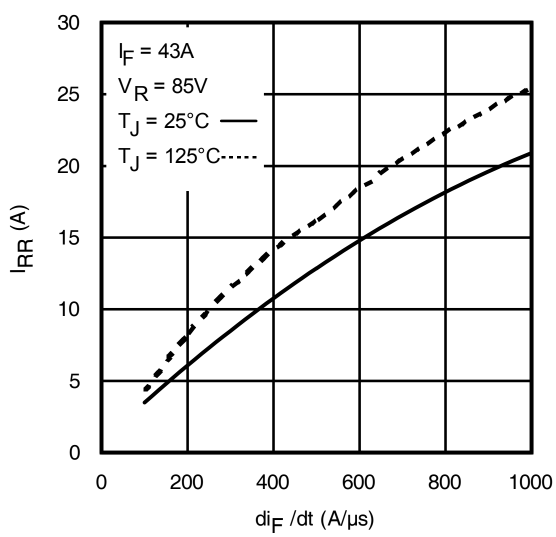


Fig 18. Typical Recovery Current vs. dif/dt

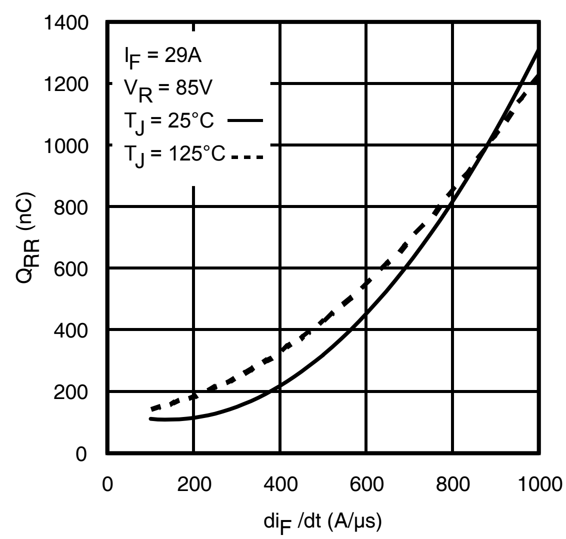


Fig 19. Typical Stored Charge vs. dif/dt

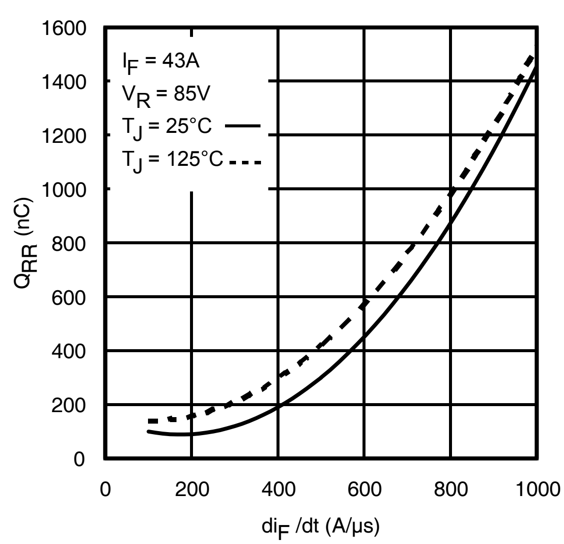


Fig 20. Typical Stored Charge vs. dif/dt

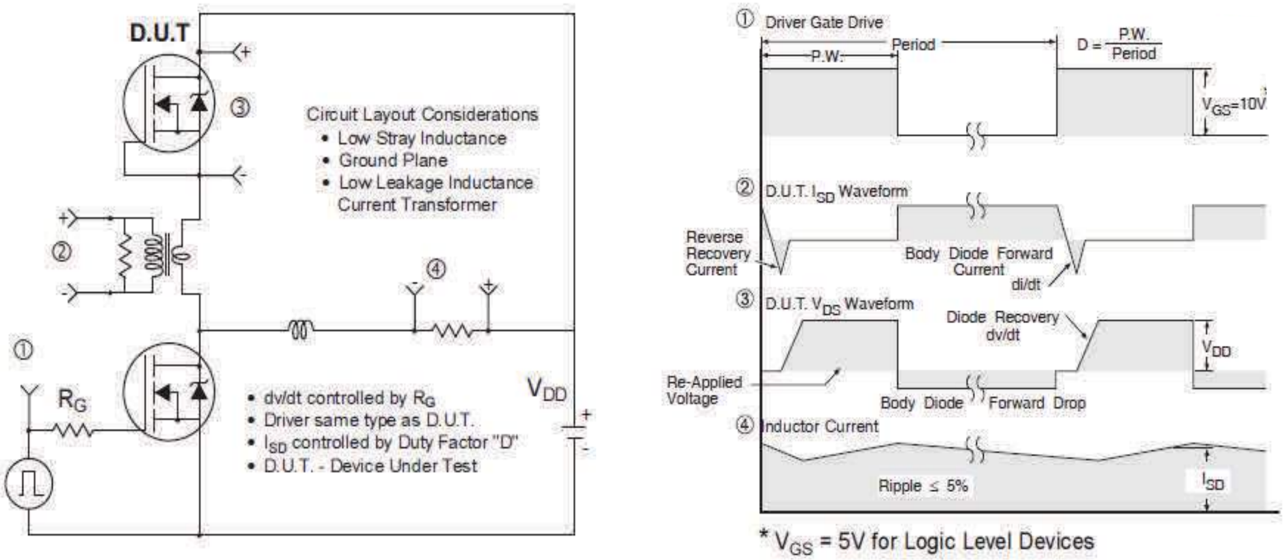


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

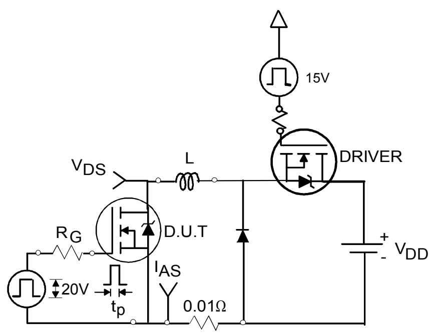


Fig 22a. Unclamped Inductive Test Circuit

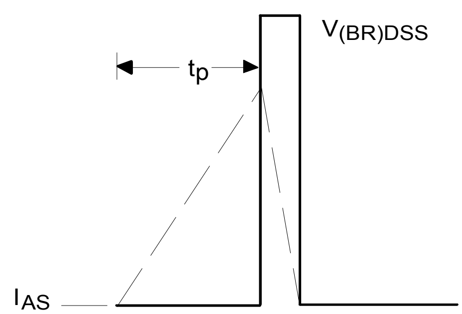


Fig 22b. Unclamped Inductive Waveforms

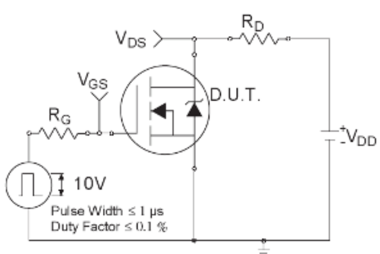


Fig 23a. Switching Time Test Circuit

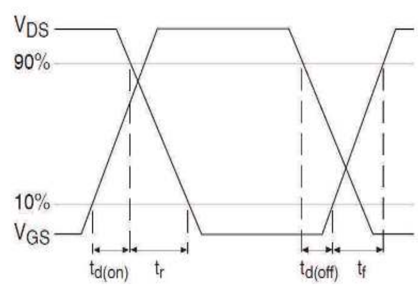


Fig 23b. Switching Time Waveforms

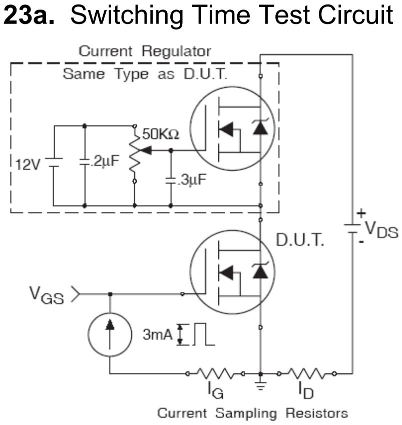


Fig 24a. Gate Charge Test Circuit

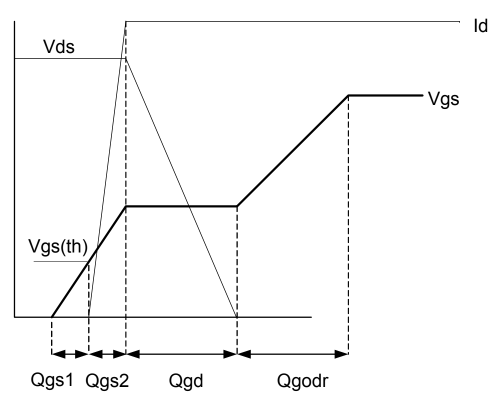
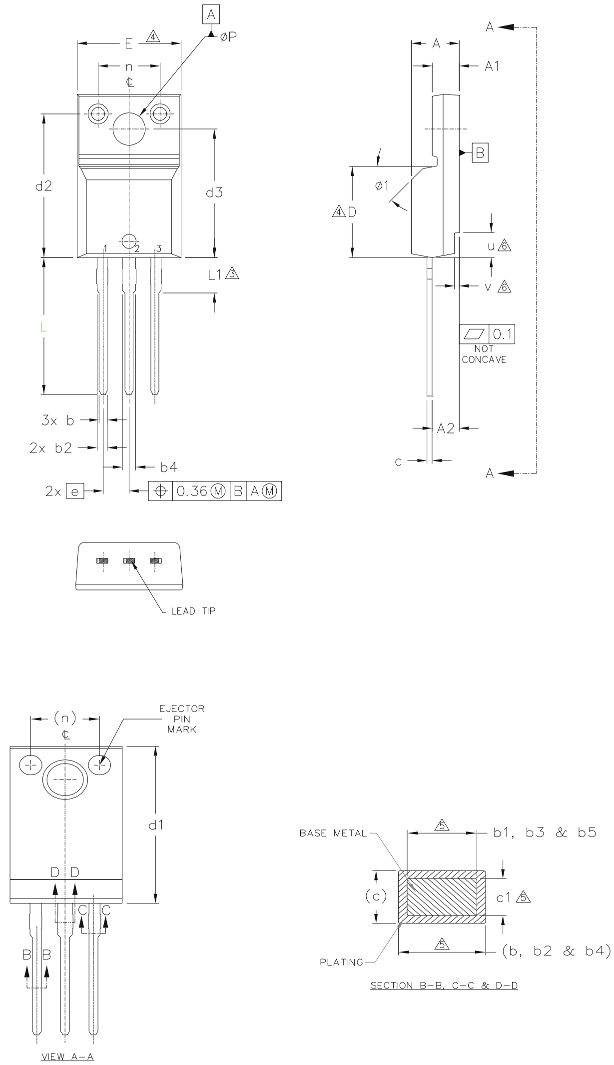


Fig 24b. Gate Charge Waveform

TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M– 1994.

2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.

4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.

5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.

6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.

7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.82	.101	.111	
A2	2.51	2.92	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	5
D	8.66	9.80	.341	.386	4
d1	15.80	16.13	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.29	12.93	.484	.509	
E	9.63	10.74	.379	.423	4
e	2.54 BSC		.100 BSC		
L	13.21	13.72	.520	.540	
L1	3.10	3.68	.122	.145	3
n	6.05	6.60	.238	.260	
øP	3.05	3.45	.120	.136	
u	2.39	2.49	.094	.098	6
v	0.41	0.51	.016	.020	6
ø1	–	45°	–	45°	

LEAD ASSIGNMENTS

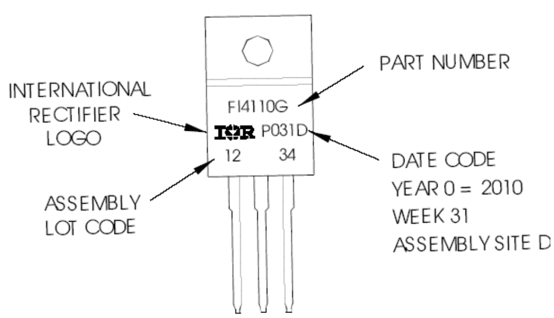
HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE

IGBTs, CoPACK
1.– GATE
2.– COLLECTOR
3.– EMITTER

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI4110G
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 31, 2010

Notes: - "P" in assembly line position indicates "Lead-Free"
- "G" suffix in part number indicates "Halogen-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at http://www.irf.com/package/

Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F) †	
Moisture Sensitivity Level	TO-220 Full-Pak	N/A
RoHS Compliant	Yes	

† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
04/27/2017	• Changed datasheet with Infineon logo - all pages. • Corrected Package Outline on page 8. • Corrected fig 19 & 20 –Y axis title from "A" to "nC" on page 6. • Added disclaimer on last page.

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